Topological states in Chevrel phase materials from first principles calculations

Shuai Zhang⁰,^{1,2} Shiyu Peng,^{1,2} Xi Dai,³ and Hongming Weng^{1,2,4,*}

¹Beijing National Laboratory for Condensed Matter Physics, and Institute of Physics, Chinese Academy of Sciences, Beijing 100190, China

²University of Chinese Academy of Sciences, Beijing 100049, China

³Department of Physics, Hong Kong University of Science and Technology, Clear Water Bay 999077, Hong Kong

⁴Songshan Lake Materials Laboratory, Dongguan, Guangdong 523808, China

(Received 28 May 2022; revised 7 July 2022; accepted 12 July 2022; published 26 July 2022)

Chevrel phase materials form a family of ternary molybdenum chalcogenides with a general chemical formula $A_x Mo_6 X_8$ (A = metal elements, X = chalcogen). The variety of A atoms makes a large number of family members and leads to many tunable physical properties, such as the superconductivity, thermoelectricity, and the ionic conductivity. In this work, we have further found various nontrivial band topological states in these materials by using first-principle calculations. The compounds having time-reversal symmetry, such as BaMo₆S₈, SrMo₆S₈, and Mo₆S₈, are topological insulators in both of the $R\bar{3}$ and $P\bar{1}$ phases, whereas EuMo₆S₈ within ferromagnetic state is an axion insulator in the $R\bar{3}$ phase and a trivial one in the $P\bar{1}$ phase. This indicates that the change of A ions can modify the chemical potential, lattice distortion, and magnetic orders, which offers a unique way to influence the topological states and other properties. We hope this work can stimulate further studies of Chevrel phase materials to find more intriguing phenomena, such as topological superconducting states and Majorana modes.

DOI: 10.1103/PhysRevB.106.035146

I. INTRODUCTION

The Chevrel phase (CP) is a ternary molybdenum chalcogenides compound family [1], which was first discovered in 1971 by Chevrel and Sergent [2]. The generic chemical formula of this family is $A_x Mo_6 X_8$. In its crystal structure, $Mo_6 X_8$ can be looked as a cluster and forms a three-dimensional (3D) network. In each cluster, six Mo atoms construct a octahedron and chalcogen atoms (X = S, Se) form a distorted pyramid ligand field around each Mo. A fills in this cluster network with x varying from 0 to 4 [1] and it can be monovalent, divalent, trivalent, or rare-earth elements. This leads to many family members and large space to tune their physical properties. Therefore, there have been lots of research done on them, and many intriguing phenomena have been found and investigated. For example, SnMo₆S₈ and PbMo₆S₈ show superconductivity at low temperature with T_c being about 14.2 and 15.2 K, respectively [3–5]. BaMo₆S₈ and EuMo₆S₈ have been found to be superconducting under pressure around several GPa [6–10]. $Ca_x Mo_6 S_8$ becomes superconducting when Ca vacancy is introduced with x = 0.94 [11]. Moreover, many of them have upper critical fields H_{c2} higher than 25 T and even up to 60 T [5,8,10], which violates the Pauli paramagnetic limit in the weak coupling Bardeen-Schrieffer-Copper superconductor [12,13]. One possible reason is the strong spin-orbit coupling (SOC) of the electrons around the Fermi level, since Mo 4d bands have been found to constitute the Fermi surface. In addition, we noticed that the resistancetemperature curve of BaMo₆S₈ shows an anomalous behavior like $ZrTe_5$ [14–17], which has sensitive topological phase

In this work, we calculated and analyzed the topological states of some sulfides in these CP materials. We have chosen four representative compounds, namely Mo₆S₈ with A site unoccupied, BaMo₆S₈ and SrMo₆S₈ with A site occupied by nonmagnetic divalent ions, and EuMo₆S₈ with A site occupied by magnetic rare-earth ions Eu. We found that some of them have nontrivial band topology and further studied their dependence on structural and magnetic phase transitions, as well as different occupation cases. On considering their unconventional superconductivity, the existence of nontrivial band topology will be very appealing, and their mutual coupling may induce topological superconductivity and Majorana modes, such as those proposed in $FeTe_{1-x}Se_x$ [22,23], the HfRuP family [24], and YCoC₂ [25].

The rest of this paper is organized as follows: First, we introduced the computational methods and software packages as well as the parameters we set. Second, we discussed the topological states of nonmagnetic compounds with BaMo₆S₈ as the representative object. Third, we studied the magnetic compound EuMo₆S₈. Finally, we present a discussion and our conclusions.

II. METHODOLOGY

We employed the Vienna Ab initio Simulation Package (VASP) [26,27] to perform the electronic structure calculations. The projector-augmented-wave (PAW) method [28,29] with the Perdew-Burke-Ernzerhof (PBE) exchangecorrelation functional [30] was used. It is known that DFT

transitions tuned by small external stimuli [18–21]. Thus, to understand these exotic physical properties, the extensive studies on their electronic structure and band topology are necessary and meaningful.

^{*}hmweng@iphy.ac.cn

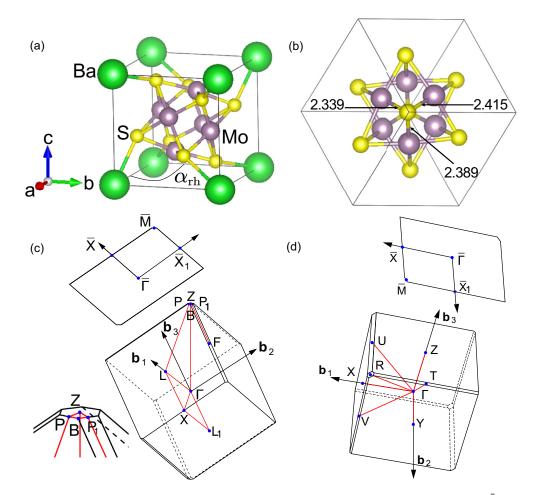


FIG. 1. Crystal structures (primitive unit cell) and Brillouin zones of BaMo₆S₈. (a) The crystal structure of the $R\bar{3}$ phase, where the green balls represent Ba and the purple (yellow) represents Mo (S). (b) The crystal structure of the $P\bar{1}$ phase in view of $\langle 111 \rangle$ direction with Ba atoms omitted for clearness. The numbers are three Mo-S bond lengths in unit of Å. Panels (c) and (d) show the bulk and the (001) surface Brillouin zones of the $R\bar{3}$ and the $P\bar{1}$ phases, respectively. The inset in panel (c) magnifies the part around the Z point.

calculation within local density approximation or generalized gradient approximation always underestimates the band gap and overestimates the band inversion. To amend this, hybrid functional HSE06 [31,32] calculation is usually employed to check the band topology [33]. The plane-wave cutoff for kinetic energy was set as 500 eV, and a $7 \times 7 \times 7$ Γ -centered Monkhorst-Pack k-point mesh was used to sample the Brillouin zone (BZ) in the self-consistent charge convergence calculation. To investigate the topological states, we constructed the Wannier functional based effective Hamiltonian using the WANNIER90 package [34], and performed the calculations of surface states and flow spectra of Wannier charge centers (WCCs) of occupied bands within Wilson loop scheme [35] using the WANNIERTOOLS package [36]. This package is also used when we check the existence of the in-gap node points. We constructed the Wannier functions for the bands composed of Mo d and S p orbitals.

III. RESULT AND DISCUSSION

A. BaMo₆S₈

The crystal structures and the BZs of $BaMo_6S_8$ are shown in Fig. 1. As most of the CP materials, it is $R\bar{3}$ phase at room temperatures and takes a structural phase transition to $P\bar{1}$ phase around 175 K [37] when temperature drops down. $R\bar{3}$ phase can be assumed as a slightly distorted cubic structure, in which the Mo₆S₈ cluster is centering the cubic lattice formed by Ba atoms. The 90° angle between the lattice vectors is reduced to 88.711° ($\alpha_{\rm rh}$) to form the $R\bar{3}$ phase [37], as shown in Fig. 1(a). The point group symmetry of $R\bar{3}$ phase is C_{3i} , where the C_3 rotation axis is along (111) direction in the rhombohedral lattice. As temperature drops down, the C_3 rotation symmetry is broken, and the symmetry reduces to $P\overline{1}$. This structural phase transition can be seen in the changes of the Mo-S bond lengths indicated in Fig. 1(b), where the three Mo-S bond lengths are different. The size of ions at A sites will affect the amplitude of distortion from C_3 symmetry. This distortion of Mo₆S₈ cluster is a kind of cooperative Jahn-Teller distortion [38] to form $P\bar{1}$ phase. All the crystal structures [37,39-45] used in work are shown in the Supplemental Material [46].

Now, let us consider the electronic structures and the topological states of the $R\bar{3}$ phase. In Fig. 2, the bands around the Fermi level are mainly from Mo 4*d* orbitals and they have been proposed to be understood in the basis set composed by molecular orbitals of Mo₆ octahedral cluster [47]. In the

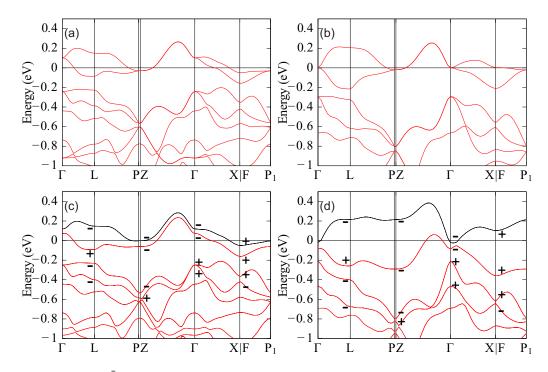


FIG. 2. The band structures of $R\bar{3}$ phase BaMo₆S₈ calculated with non-SOC PBE (a), non-SOC HSE06 (b), SOC PBE (c), and SOC HSE06 (d). In panels (c) and (d), "–" and "+" represent the parity eigenvalues of each Kramers degenerate pair at TRIMs and the red bands are the *N* occupied ones, where *N* represents the number of valence electrons of BaMo₆S₈. Here, the coordinates of these TRIMs are Γ (0, 0, 0), L (0.5, 0, 0), F (0.5, 0.5, 0), and Z (0.5, 0.5, 0.5).

non-SOC case, as shown in Fig. 2(a), the two bands crossing the Fermi level are twofold degenerated along the Γ -Z path, which is protected by the C_3 rotation symmetry, and their representation is ${}^{1}E \oplus {}^{2}E$. These two irreducible representations ${}^{1}E$ and ${}^{2}E$ are complex conjugate to each other. By taking the time-reversal symmetry into account, they will combine together to form a two dimensional irreducible representation of the type II magnetic group [48]. After including SOC, as shown in Fig. 2(c), the splitting in these two bands is obvious, namely there are finite band gaps between these two bands (each has Kramers degeneracy) at any k point in the BZ. For this reason, SOC is necessary for getting the possible band insulator state in $R\bar{3}$ phase BaMo₆S₈. Otherwise, it would be a filling-enforced metal [49,50].

Now let us consider the topological states with SOC. For convenience, we denote *N* to represent the number of valence electrons in the case of *A* being a divalent ion with x = 1, such as BaMo₆S₈. There are N - 2 valence electrons when the *A* site is empty. When SOC is considered, the Kramers degenerated (N - 1)- and *N*th bands are gapped from the (N + 1)- and (N + 2)-th bands at each *k* point, as we mentioned before. According to the Fu-Kane formula [51], we can get the topological \mathbb{Z}_2 indices $(v_0; v_1, v_2, v_3)$ from the parity eigenvalues of all occupied Kramers degenerate pairs on time-reversal invariant momenta (TRIMs).

We found if all the lowest N + 2 bands were occupied, the \mathbb{Z}_2 indices are (0; 0, 0, 0). If all the lowest N bands are occupied (i.e., the N occupation case), the \mathbb{Z}_2 indices are (1; 0, 0, 0), which means the \mathbb{Z}_2 indices for Kramers degenerated (N + 1)- and (N + 2)-th bands are (1; 0, 0, 0). If all the lowest N - 2 bands are occupied (i.e., the N - 2 occupation

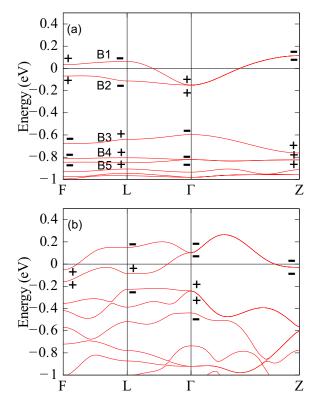


FIG. 3. (a) The non-SOC band structure calculated with scaling the lattice constants of $R\bar{3}$ phase BaMo₆S₈ by 128% and fixing the Mo₆S₈ as a rigid cluster. "B1," "B2," and so on label each flat band. The parity eigenvalues at TRIMs are also labeled. (b) The non-SOC band structure of the real BaMo₆S₈.

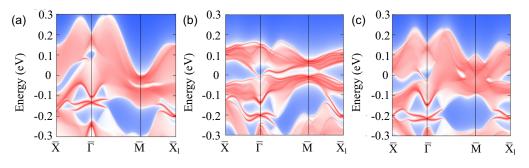


FIG. 4. The (001) surface states of $R\bar{3}$ phase BaMo₆S₈ with SOC. (a) The surface states calculated with the original band structure. (b) The surface states calculated with the renormalized band structure, which has a global gap in the *N* occupation case. (c) The surface states calculated with the renormalized band structure, which has a global gap in the *N* – 2 occupation case.

case, namely A is unoccupied), the \mathbb{Z}_2 indices are (1; 1, 1, 1), which means the \mathbb{Z}_2 indices for the (N - 1)- and Nth bands are (0; 1, 1, 1). From these \mathbb{Z}_2 indices, the gap between the group of the lowest N - 2 bands and that of N - 1 to N + 2bands is topologically nontrivial. That means there is band inversion happening between these two groups, which indicates there must be nodal line(s) in this gap in the non-SOC case [52]. The detailed calculations including the parity distribution and WCCs are shown in the Supplemental Material [46].

The band structures with HSE06 functional are shown in Figs. 2(b) and 2(d). In the non-SOC + HSE06 case, the band structure is much more like a semimetal than the PBE case, but the degeneracy of the bands crossing the Fermi level

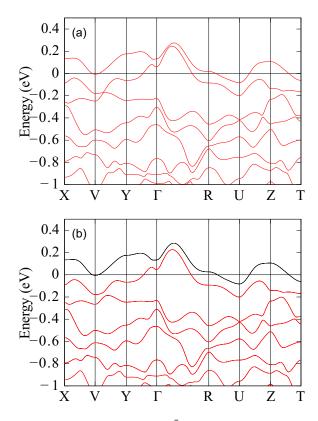


FIG. 5. The band structures of $P\bar{1}$ phase BaMo₆S₈ without SOC (a) and with SOC (b). In panel (b), the red bands are the *N* occupied bands, where *N* represents the number of valence electrons of BaMo₆S₈.

along the Γ -Z path remains. In the SOC + HSE06 case, such degeneracy is broken, and the band gap between them is much more enlarged than PBE case with small electron and hole pockets left. Comparing the parities in both cases, the parity eigenvalues and their distribution of the *N*th and the (N + 2)-th bands are not changed, as shown in Figs. 2(c) and 2(d), so the topological states from HSE06 functional are not changed.

For a better understanding of the topological states in both the N - 2 occupation and the N occupation cases, we investigated the band inversion mechanism, which provides an intuitive picture of topological phase transitions. Let us consider the non-SOC condition first. By scaling the lattice vectors by 128% and fixing the Mo₆S₈ cluster as a rigid molecular centering on the (0.5, 0.5, 0.5) inversion center, the hopping between the clusters have been reduced and we got topologically trivial flat bands as shown in Fig. 3(a). We labeled the flat bands as "B1," "B2," and so on. B1 and B2 can be represented as the elementary band representation (eBR) ${}^{1}E_{g}^{2}E_{g}@3b$. B3 is from eBR $A_{u}@3b$, and B4 and B5 are from eBR ${}^{1}E_{u}^{2}E_{u}@3b$.

To clarify the topological states in both the *N* occupation and the N - 2 occupation cases, we only need to tell which bands (i.e., B3, B4, and B5) inverted with the B1 and B2 in the real crystal because the other lower bands are not entangled with B1 and B2 until the lattice constants reduce to the real values. Comparing the parity eigenvalues at TRIMs (i.e., Γ , Z, L, and F points) in the flat bands and those in the real crystal, we can find the following:

1) At the Γ point, B1, B2 (with "+" parity eigenvalues) and B4, B5 (with "-" parity eigenvalues) are inverted.

2) At the L point, the parities of B1 and B2 change from two negative values to one negative and one positive, which means there is band inversion happens. Comparing Figs. 2(c) and 3(b), we can find that SOC can only lift the band degeneracy but not affect the parity distribution at TRIMs. The hopping between the molecular orbitals from Mo_6S_8 clusters is crucial to the band inversion.

We further calculated the (001) (rhombohedral basis) surface states of $R\bar{3}$ phase BaMo₆S₈ with SOC as shown in Fig. 4(a). Because of the absence of global gap in both *N* and *N* - 2 occupation cases, the surface Dirac cone is mixed with the bulk states. Therefore, we artificially shifted all the *ab initio* bands at every *k* point by a *k*-dependent energy value, which does not change the energy order of the bands and the

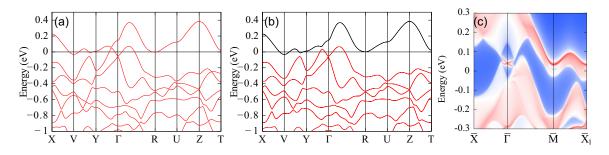


FIG. 6. The band structures without SOC (a) and with SOC (b) of $P\overline{1}$ phase SrMo₆S₈. In panel (b), the red bands are the *N* occupied ones, where *N* represents the number of the valence electrons of BaMo₆S₈. (c) The (001) surface states of $P\overline{1}$ phase SrMo₆S₈ with SOC.

band topology, but it results in a global band gap. The details of this method are described in the Supplemental Material [46]. For later convenience, we call this procedure "renormalization." We constructed two renormalized band structures which have global gap in the N and N - 2 occupation cases, respectively. Based on these renormalized band structures, we calculated the corresponding surface states with 0.02- and 0.01-eV onsite energy correction to the atoms in the surface region for the N occupation and N-2 occupation cases, respectively. As shown in Figs. 4(b) and 4(c), there is a global gap in bulk states and clear surface Dirac cones in both cases. In the N occupation case, there is only one surface Dirac cone at $\overline{\Gamma}$ and there are three surface Dirac cones in N-2occupation case at \bar{X} , $\bar{\Gamma}$, and \bar{X}_1 . The number and the distribution of surface Dirac cones are consistent with the parity distribution.

Now let us consider $P\bar{1}$ phase BaMo₆S₈. The electronic structure of $P\bar{1}$ is quite similar to the $R\bar{3}$ phase. The obvious difference is that there is no double degenerated band in the non-SOC case due to the breaking of C_3 rotation symmetry, as shown in Fig. 5(a). With the inversion symmetry retained, we can still get their topological states from Fu-Kane formula. Due to the tiny difference in both the crystal and electronic structures between $R\bar{3}$ and $P\bar{1}$ phases, the topological \mathbb{Z}_2 indices remain unchanged in both of the N - 2 occupation and N occupation cases. The detailed information (including the parity distribution, WCCs, and surface states) is shown in the Supplemental Material [46].

B. SrMo₆S₈ and Mo₆S₈

In the $R\bar{3}$ phase, the crystal structure and the band structure of SrMo₆S₈ are basically the same as $R\bar{3}$ phase BaMo₆S₈, except for the larger bandwidth of SrMo₆S₈ due to the smaller lattice constants. The topological \mathbb{Z}_2 indices of $R\bar{3}$ phase SrMo₆S₈ are the same as $R\bar{3}$ phase BaMo₆S₈ in both of the N-2 occupation and the N occupation cases. We do not repeat the discussion in the main text. The band structures and the information of the topological states of $R\bar{3}$ phase SrMo₆S₈ are shown in the Supplemental Material [46].

As shown in Figs. 6(a) and 6(b) for $P\bar{1}$ phase SrMo₆S₈, the gap between the *N*- and the (*N* + 2)-th bands at Γ point is much larger than the one in $P\bar{1}$ phase BaMo₆S₈, and there are only small electron and hole pockets near the Fermi level. This may be attributed to the subtle difference between the structures of $BaMo_6S_8$ and $SrMo_6S_8$ in the $P\overline{1}$ phase, as shown in the Supplemental Material [46].

In the *N* occupation case, the topological \mathbb{Z}_2 indices with SOC are (1;0,0,0), which are the same as $P\overline{1}$ phase BaMo₆S₈. The larger bulk band gap at Γ leads to a clear surface Dirac cone as shown in Fig. 6(c), which is calculated normally without above renormalization procedure. But for the *N* – 2 occupation case, the topological \mathbb{Z}_2 indices with SOC are (0; 1, 1, 1). They are different from those of $P\overline{1}$ phase BaMo₆S₈. The nearly closing band gap at the Γ point indicates SrMo₆S₈ is close to the topological phase transition point from (1; 1, 1, 1) to (0; 1, 1, 1) due to the crystal distortion induced by replacing Ba with smaller Sr ions.

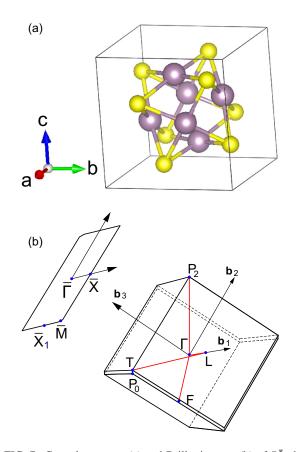


FIG. 7. Crystal structure (a) and Brillouin zone (b) of $R\overline{3}$ phase Mo₆S₈. The purple atoms and yellow atoms represent Mo and S, respectively.

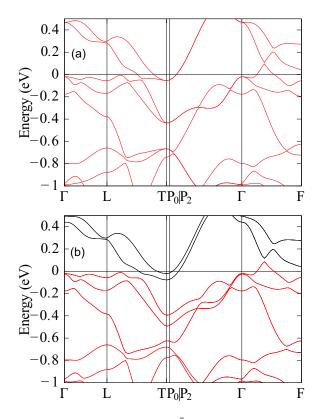


FIG. 8. The band structures of $R\overline{3}$ phase Mo₆S₈ without SOC (a) and with SOC (b). In panel (b), the red bands are the N - 2 occupied ones, where *N* represents the number of valence electrons of BaMo₆S₈.

Because the topological state of BaMo₆S₈ in the N - 2 occupation case is a strong topological insulator, it is natural to reduce two valence electrons by removing the divalent metal atoms (i.e., Ba) to get a topological insulator with a large gap near the Fermi level. This is exactly Mo₆S₈ with the *A* site empty. In the $R\bar{3}$ phase, Mo₆S₈ has a similar crystal structure to that of BaMo₆S₈. The lattice constant is 6.428 Å and $\alpha_{\rm rh}$ is large then 90° (i.e., 91.250°) [41,42]. Thus, the Brillouin zone is different from BaMo₆S₈ which have divalent metal atoms. The crystal structure and the Brillouin zone of $R\bar{3}$ phase Mo₆S₈ are shown in Fig. 7.

But from the band structures shown in Fig. 8, the gap is not as large as we expected before. The \mathbb{Z}_2 indices with SOC are (1; 1, 1, 1), which are the same as those of BaMo₆S₈ in the N - 2 occupation case. The detailed information can be found in the Supplemental Material [46].

For the $P\bar{1}$ phase, Mo₆S₈ has quite different crystal structure from BaMo₆S₈ and SrMo₆S₈ and the electronic structure is also quite different from them, as shown in Fig. 9. The \mathbb{Z}_2 indices with SOC are (1;0,0,1), which are different from BaMo₆S₈ and SrMo₆S₈ in the $P\bar{1}$ phase and the N - 2 occupation case. The parity distribution is shown in the Supplemental Material [46].

C. EuMo₆S₈

 $EuMo_6S_8$ has magnetic order at low temperatures (less than 0.4 K), but it seems not to be the simple ferromagnetic

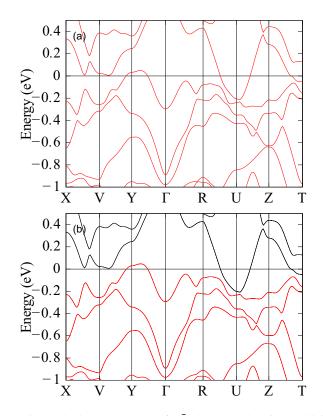


FIG. 9. The band structures of $P\bar{1}$ phase Mo₆S₈ without SOC (a) and with SOC (b). In panel (b), the red bands are the N-2 occupied ones, where N represents the number of valence electrons of BaMo₆S₈.

order [53]. The seven 4f electrons on Eu²⁺ ions are fully spin polarized and completely localized. In this sense, EuMo₆S₈ and BaMo₆S₈ are very similar, except for the breaking of the time-reversal symmetry and the Kramers degeneracy. Thus, we expect that the \mathbb{Z}_2 topological insulator in BaMo₆S₈ can be driven to axion insulator [54–57], Weyl semimetal [58–62], or trivial magnetic insulator in EuMo₆S₈. We assumed an artificial ferromagnetic order for both the $R\bar{3}$ and $P\bar{1}$ phases to investigate their topological states.

Now let us consider the $R\bar{3}$ phase first. Figure 10 shows the LDA+U band structures of EuMo₆S₈ in the ferromagnetic order. The on-site Hubbard U = 5 eV on the *f* orbitals of Eu is considered. The difference between EuMo₆S₈ and BaMo₆S₈ is the spin splitting in the band structure. The spin splitting is quite small and it does not introduce any band inversion. Therefore, the topological states of EuMo₆S₈ in both the *N* and N - 2 occupation cases are axion insulators as indicated by $z_4 = 2$, which is calculated with SOC according to the formula [63–66]

$$z_4 = \sum_K n_K^- \mod 4,\tag{1}$$

where n_K^- is the number of occupied bands with odd-parity eigenvalues at inversion-invariant momentum *K*. We also checked our results with increasing *U* to 6, 7, and 8 eV, and they are not changed.

For the $P\bar{1}$ phase, the band structures are shown in Figs. 11(a) and 11(b). In the $P\bar{1}$ phase, the z_4 indices with

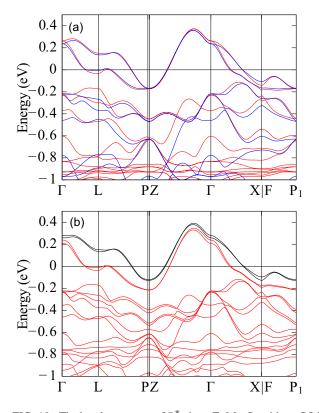


FIG. 10. The band structures of $R\bar{3}$ phase EuMo₆S₈ without SOC (a) and with SOC (b) in ferromagnetic order. In panel (a), the red blue colors represent the spin up and spin down, respectively. In panel (b), the red bands are the *N* occupied ones, where *N* represents the number of valence electrons of BaMo₆S₈. Here, the seven 4*f* electrons of Eu²⁺ are localized and not counted into the valence electrons.

SOC are 0 in both of the N - 2 and N occupation cases. This difference comes from the additional band inversion caused by structural phase transition from $R\overline{3}$ to $P\overline{1}$ phase. For the N occupation case, at Y (0.0, 0.5, 0.0), the (N - 1)- and Nth bands are inverted with the (N + 1)- and (N + 2)-th bands referring to the $R\overline{3}$ case. The (N - 1)- and Nth bands and the (N + 1)- and (N + 2)-th bands have different parity eigenvalues, leading to the topological trivial state. For the N - 2occupation case, the number of occupied bands with odd parities is reduced by two at V (0.5, 0.5, 0.0), and this results in the topological trivial state. Similarly, the topological state of $P\overline{1}$ phase is not changed with increasing U to 6, 7, and 8 eV.

IV. CONCLUSION AND DISCUSSION

We systematically studied the topological states of CP materials. For BaMo₆S₈ in both of the $R\bar{3}$ and $P\bar{1}$ phases, the topological \mathbb{Z}_2 indices are (1; 0, 0, 0) in the *N* occupation and (1; 1, 1, 1) in the *N* – 2 occupation cases. For $R\bar{3}$ phase SrMo₆S₈, the topological states are the same as $R\bar{3}$ phase BaMo₆S₈. For $P\bar{1}$ phase SrMo₆S₈, it is a strong topological insulator in the *N* occupation case, with $\mathbb{Z}_2 = (1; 0, 0, 0)$. For the *N* – 2 occupation case, it is close to a topological phase transition point between the strong and weak topological states. For Mo₆S₈ without the divalent metal atoms, it is a topological insulator and the topological invariants are the

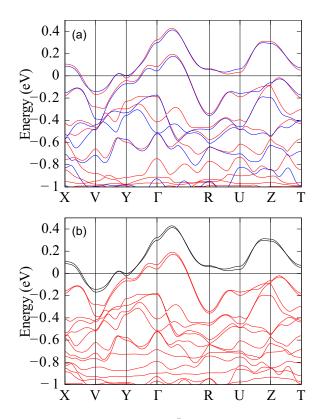


FIG. 11. The band structures of $P\bar{1}$ phase EuMo₆S₈ without SOC (a) and with SOC (b) in ferromagnetic order. In panel (a), the red and blue colors represent spin up and spin down, respectively. In panel (b), the red bands are the *N* occupied ones, where *N* represents the number of valence electrons of BaMo₆S₈. Here, the seven 4*f* electrons of Eu²⁺ are localized and not counted into the valence electrons.

same as $R\bar{3}$ phase BaMo₆S₈ in the N-2 occupation case. But in the $P\bar{1}$ phase, the topological indices are (1, 0, 0, 1), which are different from the previous compounds because of the further crystal distortion without cation ions A. For EuMo₆S₈ with ferromagnetic order, it is an axion insulator with $z_4 = 2$ in both the N and N - 2 occupation cases in the $R\bar{3}$ phase, whereas it is a trivial magnetic insulator in the $P\bar{1}$ phase because of the additional band inversion. The information of topological states of the compounds with time-reversal symmetry can also be seen in the results of the high-throughput searching of topological materials [67–71]. However, some of the results are different from ours because of the difference in detail of calculations, such as the crystal structures and the exchange-correlation functionals. Combining the intriguing physical properties of CP materials, such as high transition temperature and high upper critical field superconductivity, the nontrivial band topology revealed in this work may open another dimension in their research and provide a platform to construct topological superconductivity and Majorana modes.

ACKNOWLEDGMENTS

We acknowledge the support from the National Natural Science Foundation (Grants No. 11925408, No. 11921004, and No. 12188101), the Ministry of Science and Technology of China (Grant No. 2018YFA0305700), the Chinese Academy of Sciences (Grant No. XDB33000000), the Informatization Plan of Chinese Academy of Sciences (Grant No. CAS-WX2021SF-0102), the K. C. Wong Education Foundation (No. GJTD-2018-01), the Beijing

- O. Peña, Chevrel phases: Past, present, and future, Phys. C: Supercond. Appl. 514, 95 (2015).
- [2] R. Chevrel, M. Sergent, and J. Prigent, Sur de nouvelles phases sulfurées ternaires du molybdène, J. Solid State Chem. 3, 515 (1971).
- [3] M. Marezio, P. Dernier, J. Remeika, E. Corenzwit, and B. Matthias, Superconductivity of ternary sulfides and the structure of PbMo₆S₈, Mater. Res. Bull. 8, 657 (1973).
- [4] J. D. Jorgensen and D. G. Hinks, Low temperature structural distortion in the high T_c Chevrel-phase superconductors PbMo₆S₈ and SnMo₆S₈, Solid State Commun. 53, 289 (1985).
- [5] A. Gupta, M. Decroux, T. Willis, and Ø. Fischer, Resistivity broadening, upper critical fields, and irreversibility lines in bulk PbMo₆S₈ and SnMo₆S₈ Chevrel phase superconductors, Phys. C (Amsterdam, Neth.) 235–240, 2541 (1994).
- [6] P. Hor, M. Wu, T. Lin, X. Shao, X. Jin, and C. Chu, Pressure induced superconductivity in BaMo₆S₈, Solid State Commun. 44, 1605 (1982).
- [7] Y. S. Yao, R. P. Guertin, D. G. Hinks, J. Jorgensen, and D. W. Capone II, Superconductivity of divalent Chevrel phases at very high pressures, Phys. Rev. B 37, 5032 (1988).
- [8] Y. Y. Shu, R. Guertin, D. Capone, and D. Hinks, Upper critical field of the pressure induced superconductor BaMo₆S₈, Phys. C (Amsterdam, Neth.) 157, 247 (1989).
- [9] M. Decroux, M. S. Torikachvili, M. B. Maple, R. Baillif, Ø. Fischer, and J. Muller, Experimental evidence for bulk superconductive behavior of EuMo₆S₈ under pressure, Phys. Rev. B 28, 6270 (1983).
- [10] M. Decroux, S. E. Lambert, M. S. Torikachvili, M. B. Maple, R. P. Guertin, L. D. Woolf, and R. Baillif, Observation of Bulk Superconductivity in EuMo₆S₈ under Pressure, Phys. Rev. Lett. 52, 1563 (1984).
- [11] C. Geantet, J. Padiou, O. Peña, M. Sergent, and R. Horyn, Evidence of superconductivity in $Ca_x^{2+}Mo_6S_8$ single crystals at normal pressure, Solid State Commun. **64**, 1363 (1987).
- [12] K. Ma, K. Gornicka, R. Lefèvre, Y. Yang, H. M. Rønnow, H. O. Jeschke, T. Klimczuk, and F. O. von Rohr, Superconductivity with high upper critical field in the cubic centrosymmetric η -carbide Nb₄Rh₂C_{1- δ}, ACS Mater. Au **1**, 55 (2021).
- [13] M. Tinkham, *Introduction to Superconductivity* (Dover Publications, Mineola, New York, 2004).
- [14] H. W. Meul, On the unusual physical properties of europiumbased molybdenum chalcogenides and related Chevrel compounds, Helv. Phys. Acta 59, 417 (1986).
- [15] C. Rossel, M. Maple, H. Meul, Ø. Fischer, X. Zhang, and N. Ong, Transport and magnetic properties of BaMo₆S₈: Some evidence for charge-density waves, Phys. B+C (Amsterdam, Neth.) 135, 381 (1985).
- [16] E. P. Stillwell, A. C. Ehrlich, G. N. Kamm, and D. J. Gillespie, Effect of elastic tension on the electrical resistance of $HfTe_5$ and $ZrTe_5$, Phys. Rev. B **39**, 1626 (1989).

Natural Science Foundation (No. Z180008), and the Beijing Municipal Science and Technology Commission (No. Z191100007219013). X.D. acknowledges financial support from the Hong Kong Research Grants Council (Projects No. GRF16300918 and No. 16309020).

- [17] E. Skelton, T. Wieting, S. Wolf, W. Fuller, D. Gubser, T. Francavilla, and F. Levy, Giant resistivity and x-ray diffraction anomalies in low-dimensional ZrTe₅ and HfTe₅, Solid State Commun. 42, 1 (1982).
- [18] H. Weng, X. Dai, and Z. Fang, Transition-Metal Pentatelluride ZrTe₅ and HfTe₅: A Paradigm for Large-Gap Quantum Spin Hall Insulators, Phys. Rev. X 4, 011002 (2014).
- [19] Y. Zhang, C. Wang, L. Yu, G. Liu, A. Liang, J. Huang, S. Nie, X. Sun, Y. Zhang, B. Shen, J. Liu, H. Weng, L. Zhao, G. Chen, X. Jia, C. Hu, Y. Ding, W. Zhao, Q. Gao, C. Li *et al.*, Electronic evidence of temperature-induced Lifshitz transition and topological nature in ZrTe₅, Nat. Commun. 8, 15512 (2017).
- [20] C. Vaswani, L.-L. Wang, D. H. Mudiyanselage, Q. Li, P. M. Lozano, G. D. Gu, D. Cheng, B. Song, L. Luo, R. H. J. Kim, C. Huang, Z. Liu, M. Mootz, I. E. Perakis, Y. Yao, K. M. Ho, and J. Wang, Light-Driven Raman Coherence as a Nonthermal Route to Ultrafast Topology Switching in a Dirac Semimetal, Phys. Rev. X 10, 021013 (2020).
- [21] L. Luo, D. Cheng, B. Song, L.-L. Wang, C. Vaswani, P. M. Lozano, G. Gu, C. Huang, R. H. J. Kim, Z. Liu, J.-M. Park, Y. Yao, K. Ho, I. E. Perakis, Q. Li, and J. Wang, A light-induced phononic symmetry switch and giant dissipationless topological photocurrent in ZrTe₅, Nat. Mater. **20**, 329 (2021).
- [22] Z. Wang, P. Zhang, G. Xu, L. K. Zeng, H. Miao, X. Xu, T. Qian, H. Weng, P. Richard, A. V. Fedorov, H. Ding, X. Dai, and Z. Fang, Topological nature of the FeSe_{0.5}Te_{0.5} superconductor, Phys. Rev. B **92**, 115119 (2015).
- [23] P. Zhang, K. Yaji, T. Hashimoto, Y. Ota, T. Kondo, K. Okazaki, Z. Wang, J. Wen, G. D. Gu, H. Ding, and S. Shin, Observation of topological superconductivity on the surface of an iron-based superconductor, Science 360, 182 (2018).
- [24] Y. Qian, S. Nie, C. Yi, L. Kong, C. Fang, T. Qian, H. Ding, Y. Shi, Z. Wang, H. Weng, and Z. Fang, Topological electronic states in HfRuP family superconductors, Npj Comput. Mater. 5, 121 (2019).
- [25] Y. Xu, Y. Gu, T. Zhang, C. Fang, Z. Fang, X.-L. Sheng, and H. Weng, Topological nodal lines and hybrid Weyl nodes in YCoC₂, APL Mater. 7, 101109 (2019).
- [26] G. Kresse and J. Furthmüller, Efficient iterative schemes for *ab initio* total-energy calculations using a plane-wave basis set, Phys. Rev. B 54, 11169 (1996).
- [27] G. Kresse and J. Furthmüller, Efficiency of *ab-initio* total energy calculations for metals and semiconductors using a plane-wave basis set, Comput. Mater. Sci. 6, 15 (1996).
- [28] P. E. Blöchl, Projector augmented-wave method, Phys. Rev. B 50, 17953 (1994).
- [29] G. Kresse and D. Joubert, From ultrasoft pseudopotentials to the projector augmented-wave method, Phys. Rev. B 59, 1758 (1999).
- [30] J. P. Perdew, K. Burke, and M. Ernzerhof, Generalized Gradient Approximation Made Simple, Phys. Rev. Lett. 77, 3865 (1996).

- [31] J. Heyd, G. E. Scuseria, and M. Ernzerhof, Hybrid functionals based on a screened coulomb potential, J. Chem. Phys. 118, 8207 (2003).
- [32] J. Heyd and G. E. Scuseria, Efficient hybrid density functional calculations in solids: Assessment of the Heyd-Scuseria-Ernzerhof screened coulomb hybrid functional, J. Chem. Phys. 121, 1187 (2004).
- [33] J. Vidal, X. Zhang, L. Yu, J.-W. Luo, and A. Zunger, False-positive and false-negative assignments of topological insulators in density functional theory and hybrids, Phys. Rev. B 84, 041109(R) (2011).
- [34] G. Pizzi, V. Vitale, R. Arita, S. Blügel, F. Freimuth, G. Géranton, M. Gibertini, D. Gresch, C. Johnson, T. Koretsune, J. Ibañez-Azpiroz, H. Lee, J.-M. Lihm, D. Marchand, A. Marrazzo, Y. Mokrousov, J. I. Mustafa, Y. Nohara, Y. Nomura, L. Paulatto *et al.*, WANNIER90 as a community code: New features and applications, J. Phys.: Condens. Matter **32**, 165902 (2020).
- [35] R. Yu, X. L. Qi, A. Bernevig, Z. Fang, and X. Dai, Equivalent expression of \mathbb{Z}_2 topological invariant for band insulators using the non-Abelian Berry connection, Phys. Rev. B **84**, 075119 (2011).
- [36] Q. Wu, S. Zhang, H.-F. Song, M. Troyer, and A. A. Soluyanov, WANNIERTOOLS: An open-source software package for novel topological materials, Comput. Phys. Commun. 224, 405 (2018).
- [37] J. D. Jorgensen and D. G. Hinks, Rhombohedral-to-triclinic phase transition in BaMo₆S₈, Phys. B+C (Amsterdam, Neth.) 136, 485 (1986).
- [38] S. Zhang, T. Zhang, H. Deng, Y. Ding, Y. Chen, and H. Weng, Crystal and electronic structure of $GaTa_4Se_8$ from first-principles calculations, Phys. Rev. B **102**, 214114 (2020).
- [39] W. Kalsbach, Strukturelle Phasenübergänge und druckinduzierte Supraleitung von Molybdän-Clusterverbindungen (Chevrel-Phasen), Tech. Rep. Juel-1921, Jülich, 1984.
- [40] B. Koppelhuber-Bitschnau, F. A. Mautner, and K. Yvon, Lowtemperature structural phase transition in SrMo₆S₈ studied by x-ray powder diffraction, Monatsh. Chem. Chem. Monthly 121, 505 (1990).
- [41] Mo₆S₈ (Mo₃S₄ rhom) crystal structure: Data sheet, *Pauling File Multinaries Edition*, 2012 (Springer-Verlag, Berlin, 2016).
- [42] W. R. McKinnon and J. R. Dahn, Structure and electrochemistry of Li_xMo₆S₈, Phys. Rev. B **31**, 3084 (1985).
- [43] H. Fukuoka, K. Masuoka, T. Hanaoka, and K. Inumaru, New polymorph of Mo₃S₄ prepared using a high-pressure synthesis technique: Crystal structure, electronic property, and band calculation, Inorg. Chem. 52, 7918 (2013).
- [44] Ø. Fischer, A. Treyvaud, R. Chevrel, and M. Sergent, Superconductivity in the $\text{Re}_x\text{Mo}_6S_8$, Solid State Commun. **17**, 721 (1975).
- [45] S. Quezel, P. Burlet, A. Dinia, J. Rossat-Mignod, R. Horyn, O. Pena, and M. Sergent, Neutron diffraction study of the crystal and magnetic structures of ¹⁵³EuMo₆S₈, Phys. B: Condens. Matter 156–157, 780 (1989).
- [46] See Supplemental Material at http://link.aps.org/supplemental/ 10.1103/PhysRevB.106.035146 for the crystal structure, description of the procedure of band structure renormalization, and more information about the band topology.

- [47] H. Nohl, W. Klose, and O. K. Andersen, Band Structures of M_xMo₆X₈- and M₂Mo₆X₆- Cluster Compounds, in *Superconductivity in ternary compounds I* (Springer, Berlin, 1982), pp. 165–221.
- [48] M. El-Batanouny and F. Wooten, Symmetry and Condensed Matter Physics: A Computational Approach (Cambridge University Press, Cambridge, UK, 2008).
- [49] H. Watanabe, H. C. Po, M. P. Zaletel, and A. Vishwanath, Filling-Enforced Gaplessness in Band Structures of the 230 Space Groups, Phys. Rev. Lett. 117, 096404 (2016).
- [50] R. Chen, H. C. Po, J. B. Neaton, and A. Vishwanath, Topological materials discovery using electron filling constraints, Nat. Phys. 14, 55 (2018).
- [51] L. Fu and C. L. Kane, Topological insulators with inversion symmetry, Phys. Rev. B 76, 045302 (2007).
- [52] Z. Song, T. Zhang, and C. Fang, Diagnosis for Nonmagnetic Topological Semimetals in the Absence of Spin-Orbital Coupling, Phys. Rev. X 8, 031069 (2018).
- [53] T. Takabatake, R. W. McCallum, M. Kubota, and F. Pobell, Low-temperature magnetic properties of EuMo₆S₈ and EuMo₆Se₈, J. Low Temp. Phys. 55, 111 (1984).
- [54] R. D. Peccei and H. R. Quinn, CP Conservation in the Presence of Pseudoparticles, Phys. Rev. Lett. 38, 1440 (1977).
- [55] A. M. Essin, J. E. Moore, and D. Vanderbilt, Magnetoelectric Polarizability and Axion Electrodynamics in Crystalline Insulators, Phys. Rev. Lett. **102**, 146805 (2009).
- [56] J. Langbehn, Y. Peng, L. Trifunovic, F. von Oppen, and P. W. Brouwer, Reflection-Symmetric Second-Order Topological Insulators and Superconductors, Phys. Rev. Lett. **119**, 246401 (2017).
- [57] Y. Xu, Z. Song, Z. Wang, H. Weng, and X. Dai, Higher-Order Topology of the Axion Insulator EuIn₂As₂, Phys. Rev. Lett. 122, 256402 (2019).
- [58] H. Weng, C. Fang, Z. Fang, B. A. Bernevig, and X. Dai, Weyl Semimetal Phase in Noncentrosymmetric Transition-Metal Monophosphides, Phys. Rev. X 5, 011029 (2015).
- [59] B. Q. Lv, H. M. Weng, B. B. Fu, X. P. Wang, H. Miao, J. Ma, P. Richard, X. C. Huang, L. X. Zhao, G. F. Chen, Z. Fang, X. Dai, T. Qian, and H. Ding, Experimental Discovery of Weyl Semimetal TaAs, Phys. Rev. X 5, 031013 (2015).
- [60] X. Wan, A. M. Turner, A. Vishwanath, and S. Y. Savrasov, Topological semimetal and Fermi-arc surface states in the electronic structure of pyrochlore iridates, Phys. Rev. B 83, 205101 (2011).
- [61] G. Xu, H. Weng, Z. Wang, X. Dai, and Z. Fang, Chern Semimetal and the Quantized Anomalous Hall Effect in HgCr₂Se₄, Phys. Rev. Lett. **107**, 186806 (2011).
- [62] Y. Hu, C. Yue, D. Yuan, J. Gao, Z. Huang, Z. Fang, C. Fang, H. Weng, and W. Zhang, The evolution of Weyl nodes in Ni doped thallium niobate pyrochlore Tl_{2-x}Ni_xNb₂O₇, arXiv:2112.04127 [cond-mat.mtrl-sci].
- [63] A. M. Turner, Y. Zhang, R. S. K. Mong, and A. Vishwanath, Quantized response and topology of magnetic insulators with inversion symmetry, Phys. Rev. B 85, 165120 (2012).
- [64] H. Watanabe, H. C. Po, and A. Vishwanath, Structure and topology of band structures in the 1651 magnetic space groups, Sci. Adv. 4, eaat8685 (2018).

- [65] S. Ono and H. Watanabe, Unified understanding of symmetry indicators for all internal symmetry classes, Phys. Rev. B 98, 115150 (2018).
- [66] Y. Xu, L. Elcoro, Z.-D. Song, B. J. Wieder, M. G. Vergniory, N. Regnault, Y. Chen, C. Felser, and B. A. Bernevig, Highthroughput calculations of magnetic topological materials, Nature (London) 586, 702 (2020).
- [67] B. Bradlyn, L. Elcoro, J. Cano, M. G. Vergniory, Z. Wang, C. Felser, M. I. Aroyo, and B. A. Bernevig, Topological quantum chemistry, Nature (London) 547, 298 (2017).
- [68] M. G. Vergniory, L. Elcoro, C. Felser, N. Regnault, B. A. Bernevig, and Z. Wang, A complete catalogue of

high-quality topological materials, Nature (London) **566**, 480 (2019).

- [69] M. G. Vergniory, B. J. Wieder, L. Elcoro, S. S. P. Parkin, C. Felser, B. A. Bernevig, and N. Regnault, All topological bands of all nonmagnetic stoichiometric materials, Science 376, eabg9094 (2022).
- [70] T. Zhang, Y. Jiang, Z. Song, H. Huang, Y. He, Z. Fang, H. Weng, and C. Fang, Catalogue of topological electronic materials, Nature (London) 566, 475 (2019).
- [71] F. Tang, H. C. Po, A. Vishwanath, and X. Wan, Comprehensive search for topological materials using symmetry indicators, Nature (London) 566, 486 (2019).